## **Vishay Semiconductors**

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## Thyristor High Voltage, Phase Control SCR, 50 A



PRIMARY CHARACTERISTICS								
I <sub>T(AV)</sub> 50 A								
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V							
V <sub>TM</sub> (typ.)	1.2 V							
I <sub>GT</sub> (typ.)	45 mA							
T <sub>J</sub> max.	150 °C							
Package	TO-247AD 3L							
Circuit configuration	Single SCR							

### **FEATURES**

- AEC-Q101 qualified, meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification



HALOGEN

- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **APPLICATIONS**

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

### DESCRIPTION

The VS-50TPS12 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications.

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage	V <sub>RRM</sub> / V <sub>DRM</sub>		1200	V					
On-state voltage	V <sub>T</sub>	50 A, T <sub>J</sub> = 125 °C	1.2	v					
Average rectified forward current	I <sub>T(AV)</sub>		50						
Maximum continuous RMS on-state current	I <sub>RMS</sub>		79	А					
Non-repetitive peak surge current	I <sub>TSM</sub>		630						
Maximum rate of rise	dv/dt		1000	V/µs					
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +150	°C					

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> / V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> / I <sub>DRM</sub> AT 150 °C mA						
VS-50TPS12LHM3	1200	1300	70						

# VS-50TPS12LHM3



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ABSOLUTE MAXIMUM RATING	S					
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	$T_C = 112 \ ^{\circ}C$ , 180° conduction half sine v	vave	-	50	
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>					
Peak, one-cycle non-repetitive surge current	L	10 ms sine pulse, rated $V_{\text{RRM}}$ applied		-	530	
Feak, one-cycle non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	Initial $T_J = T_J$	-	630	
I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated $V_{RRM}$ applied	maximum	-	1405	A <sup>2</sup> s
I-t for fusing	1-1	10 ms sine pulse, no voltage reapplied		-	1986	A-5
I <sup>2</sup> √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied, $T_J = 125 \text{ °C}$			19 850	A²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>		-	0.89	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	T 105 %	-	0.97		
Low level value of on-state slope resistance	r <sub>t1</sub>	T <sub>J</sub> = 125 °C	-	6.77		
High level value of on-state slope resistance	r <sub>t2</sub>			-	6.32	mΩ
	V	50 A, T <sub>J</sub> = 25 °C		1.2	1.32	V
On-state voltage	V <sub>T</sub>	100 A, T <sub>J</sub> = 25 °C			1.6	v
Rate of rise of turned-on current	di/dt	T <sub>J</sub> = 25 °C		-	150	A∕µs
Holding current	Ι <sub>Η</sub>	Anode supply 6 V resistive load T	DE °C	-	300	
Latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$		-	350	
Deverse and direct lockage overset	1 /1	T <sub>J</sub> = 25 °C			0.05	mA
Reverse and direct leakage current	I <sub>RRM</sub> /I <sub>DRM</sub>	T <sub>J</sub> = 150 °C			70	
Rate of rise of off-state voltage	dv/dt	$T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ ,	$R_g$ -k = 100 $\Omega$	-	1000	V/µs

TRIGGERING											
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS					
Peak gate power	P <sub>GM</sub>	10 ma aina pula	no voltage reapplied	-	10	w					
Average gate power	P <sub>G(AV)</sub>	TO THS SITTE PUIS	se, no voltage reapplied	-	2.5	vv					
Peak gate current	I <sub>GM</sub>			-	2.5	Α					
Peak negative gate voltage	-V <sub>GM</sub>			-	10						
		T <sub>J</sub> = -40 °C	Anode supply = 6 V resistive load	-	1.6	v					
Required DC gate voltage to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C		-	1.5	v					
		T <sub>J</sub> = 150 °C		-	1						
		T <sub>J</sub> = -40 °C		-	160						
Required DC gate to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	45	100	mA					
		T <sub>J</sub> = 150 °C		-	60						
DC gate voltage not to trigger	V <sub>GD</sub>	T <sub>.I</sub> = 150 °C, V <sub>DBM</sub> = rated value		-	0.2	V					
DC gate current not to trigger	I <sub>GD</sub>	$I_{\rm J} = 150 {}^{\rm PC},  V_{\rm D}$	-	3	mA						

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Turn-on time	t <sub>gt</sub>	$I_{T}$ = 50 A, $V_{D}$ = 50 % $V_{DRM},$ $I_{gt}$ = 300 mA, $T_{J}$ = 25 $^{\circ}\text{C}$	1.5	-	
Turn-off time	tq	$ I_{T} = 50 \text{ A}, V_{D} = 80 \ \% \ V_{DRM}, \ dV/dt = 20 \ V/\mu s, \ t_{p} = 200 \ \mu s \\ I_{gt} = 100 \ mA, \ dI/dt = 10 \ A/\mu s, \ V_{R} = 100 \ V, \ T_{J} = 150 \ ^{\circ}C $	92	-	μs

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THERMAL AND MECHANICAL SPECIFICATIONS											
PARAMETER		SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS					
Maximum junction and storage ter	mperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40	150	°C					
Maximum thermal resistance, junction to case		R <sub>thJC</sub>		-	0.35						
Maximum thermal resistance, junc	Maximum thermal resistance, junction to ambient			-	40	°C/W					
Typical thermal resistance, case to	o heatsink	R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.2	-						
Mounting torgue	minimum			6	(5)	kgf · cm					
Mounting torque	maximum			12 (10)		(lbf · in)					
Marking device			Case style Super TO-247AD 3L	į	50TPS12L	Н					

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DEVICE	S	INE HALF	WAVE CO	NDUCTIO	N	RECTANGULAR WAVE CONDUCTION					UNITS
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-50TPS12LHM3	0.143	0.166	0.208	0.299	0.490	0.099	0.168	0.223	0.311	0.494	°C/W

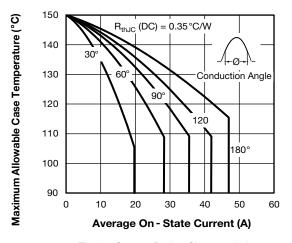


Fig. 1 - Current Rating Characteristics

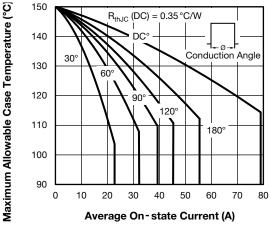


Fig. 2 - Current Rating Characteristics

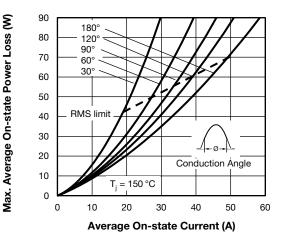


Fig. 3 - On-State Power Loss Characteristics

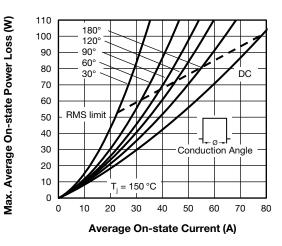


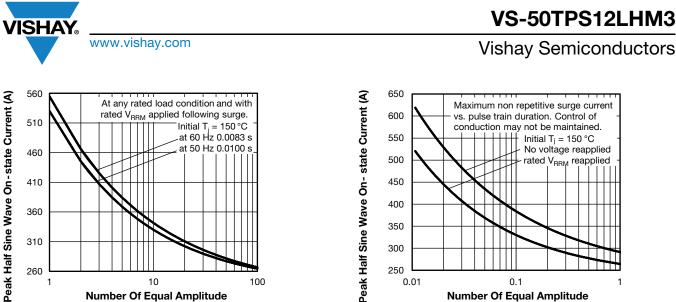
Fig. 4 - On-State Power Loss Characteristics

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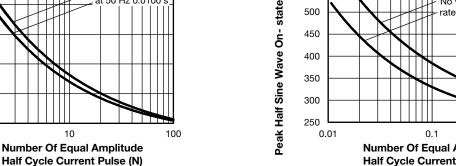
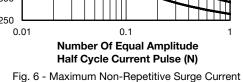
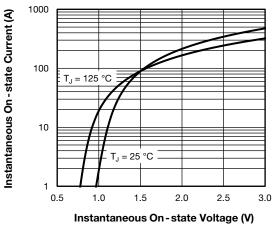


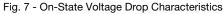
Fig. 5 - Maximum Non-Repetitive Surge Current

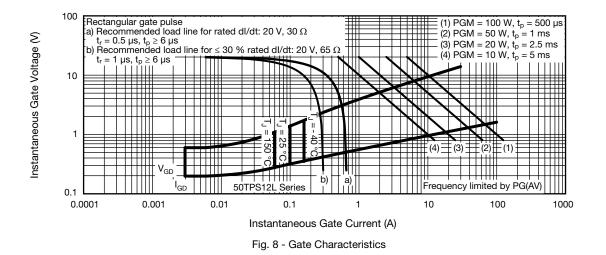
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## VS-50TPS12LHM3

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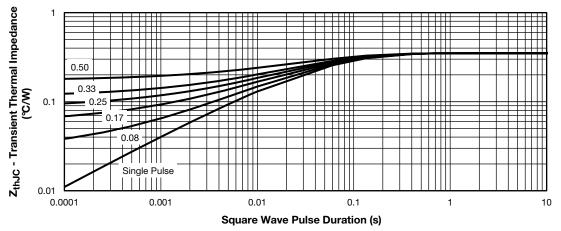


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

### **ORDERING INFORMATION TABLE**

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Device code	VS-	50	т	Р	s	12	L	н	М3
	1	2	3	4	5	6	7	8	9
	1 - 2 - 3 - 4 - 5 -	Cur Circ T = P =	rent coor cuit conf thyristo TO-247 e of silio	AD pac	50 A) n: kage				
	6 - 7 - 8 -	Volt Pac	age coo kage L	rd recove de (12 = = long le 101 qua	1200 V ead				
	9 -	M3	= halog	en-free,	RoHS-	complia	nt, and	termina	tions lea

ORDERING INFORMATION (example)										
PREFERRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION										
VS-50TPS12LHM3	25	contact factory	Antistatic plastic tubes							

LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95626							
Part marking information	TO-247AD 3L	www.vishay.com/doc?95007						

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TO-247AD 3L

### **DIMENSIONS** in millimeters and inches



View B

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
с	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

(2, 52, 51) (4) Section C - C, D - D, E - E

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215 BSC		
ØК	0.254		0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØР	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

- <sup>(3)</sup> Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- <sup>(5)</sup> Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- <sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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